Contents STx8NM60N

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STx8NM60N Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum ratings

		Value		
Symbol	Parameter	TO-220, IPAK, DPAK, D²PAK	TO-220FP	Unit
$V_{DS}$	Drain-source voltage (V <sub>GS</sub> = 0)	600		V
V <sub>GS</sub>	Gate-source voltage	± 25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	7	7 (1)	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	4.3	4.3 (1)	Α
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	28	28 (1)	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	70	25	W
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1 \text{ s;T}_C = 25 ^{\circ}\text{C}$ )	50/81	2500	V
dv/dt (3)	Peak diode recovery voltage slope	15		V/ns
T <sub>j</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to 1	50	°C

- 1. Limited only by maximum temperature allowed
- 2. Pulse width limited by safe operating area
- 3.  $I_{SD} \leq$  7 A, di/dt  $\leq$  400 A/ $\mu$ s,  $V_{DD}$  = 80%  $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value					Unit
Symbol	Faranteter	TO-220	IPAK	DPAK	D <sup>2</sup> PAK	TO-220FP	Offic
Rthj-case	Thermal resistance junction-case	1.78			5	°C/W	
Rthj-amb	Thermal resistance junction-amb	62.5	100		(	62.5	°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose			300			°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I <sub>AS</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj max)	2.5	А
E <sub>AS</sub>	Single pulse avalanche energy (starting Tj = 25 °C, $I_D = I_{AS}$ , $V_{DD} = 50 \text{ V}$ )	200	mJ

Electrical characteristics STx8NM60N

## 2 Electrical characteristics

(T<sub>CASE</sub>=25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			٧
dv/dt <sup>(1)</sup>	Drain-source voltage slope	$V_{DD} = 480 \text{ V}, I_{D} = 7 \text{ A},$ $V_{GS} = 10 \text{ V}$		38		V/ns
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS}$ = Max rating, $V_{DS}$ = Max rating, Tc = 125 °C		10	1 100	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20 V	00	5	±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	٧
R <sub>DS(on)</sub>	Static drain-source on resistance	$V_{GS} = 10V, I_D = 3.5 A$		0.56	0.65	Ω

<sup>1.</sup> Characteristics value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 3.5 \text{ A}$		15		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V, f} = 1 \text{ MHz, V}_{GS} = 0$		560 37 2		pF pF pF
Coss eq. (2)	Equivalent output capacitance	$V_{GS} = 0$ , $V_{DS} = 0$ to 480 V		153		pF
$R_{G}$	Gate input resistance	f = 1 MHz Gate DC Bias = 0 Test Signal Level = 20 mV Open Drain		6		Ω
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}$ = 480 V, $I_D$ = 7 A $V_{GS}$ = 10 V (see Figure 19)		19 3 10		nC nC nC

<sup>1.</sup> Pulsed: pulse duration = 300µs, duty cycle 1.5%

<sup>2.</sup>  $C_{oss\ eq}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ 

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time	$V_{DD} = 300 \text{ V}, I_D = 3.5 \text{ A},$		10		ns
t <sub>r</sub>	Rise time	$R_G = 4.7 \Omega, V_{GS} = 10 V$		12		ns
t <sub>d(off)</sub>	Turn-off delay time	(see Figure 18),		40		ns
t <sub>f</sub>	Fall time	(see Figure 23)		10		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>SD</sub>	Source-drain current Source-drain current (pulsed)			(	7 28	A A
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	$I_{SD} = 7 A, V_{GS} = 0$	.0	90	1.3	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	I <sub>SD</sub> = 7 A, di/dt = 100 A/μs, V <sub>DD</sub> = 30 V, Tj = 25 °C (see Figure 20)		310 2.40 15		ns μC A
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ = 7A, di/dt = 100 A/ $\mu$ s, V <sub>DD</sub> = 30 V, Tj=150°C (see Figure 20)		480 3.50 15		ns μC Α

<sup>1.</sup> Pulse width limited by safe operating area

<sup>2.</sup> Pulsed: pulse duration = 300µs, duty cycle 1.5%

Electrical characteristics STx8NM60N

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, Figure 3. Thermal impedance for TO-220, D²PAK

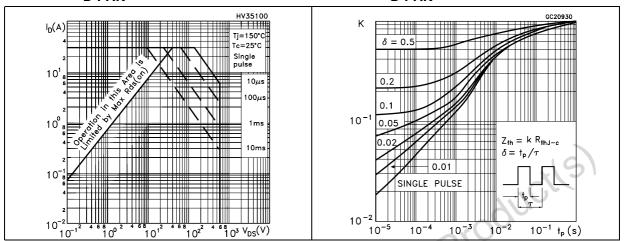


Figure 4. Safe operating area for DPAK, IPAK Figure 5. Thermal impedance for DPAK, IPAK

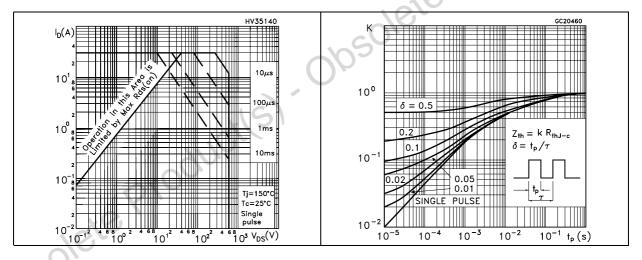


Figure 6. Safe operating area for TO-220FP Figure 7. Thermal impedance for TO-220FP

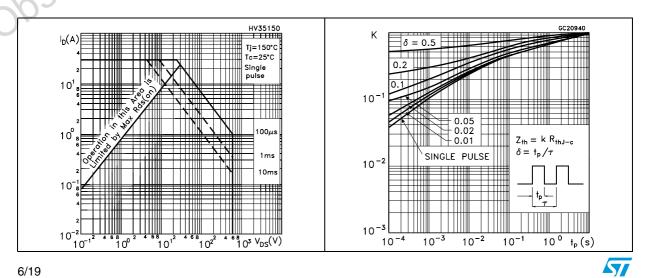
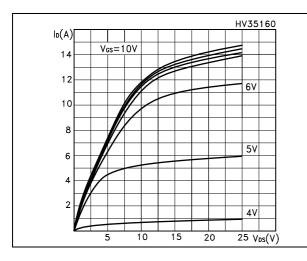


Figure 8. Output characteristics

Figure 9. Transfer characteristics



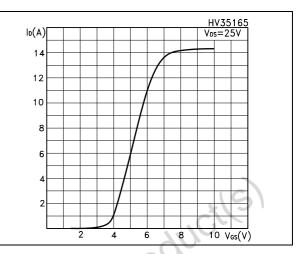
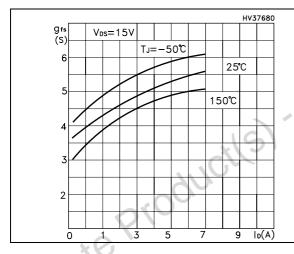


Figure 10. Transconductance

Figure 11. Static-drain source on resistance



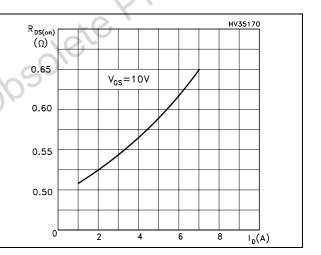
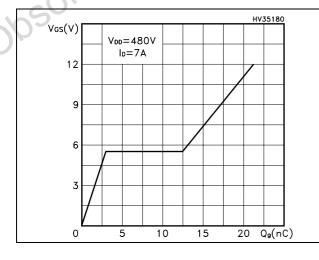
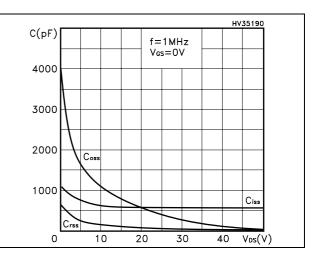


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations





Electrical characteristics STx8NM60N

Figure 14. Normalized gate threshold voltage Figure 15. Normalized on resistance vs vs temperature temperature

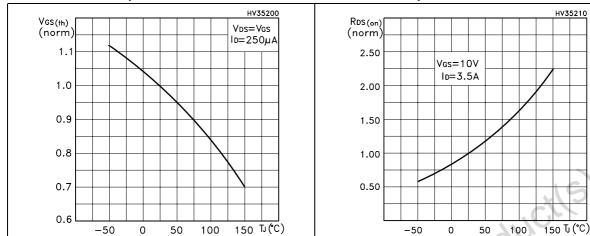
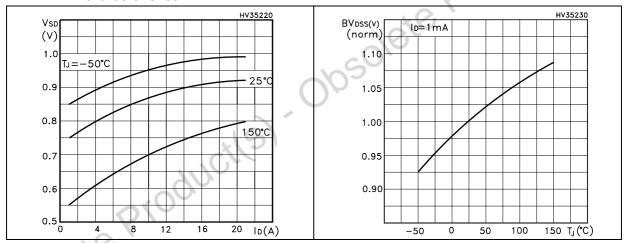


Figure 16. Source-drain diode forward characteristics

Figure 17. Normalized  $BV_{DSS}$  vs temperature



STx8NM60N Test circuit

## 3 Test circuit

Figure 18. Switching times test circuit for resistive load

Figure 19. Gate charge test circuit

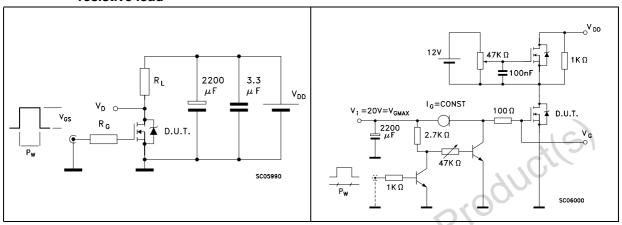


Figure 20. Test circuit for inductive load switching and diode recovery times

Figure 21. Unclamped inductive load test circuit

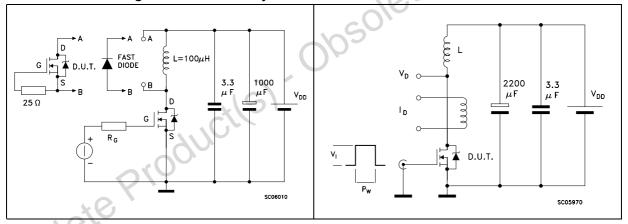
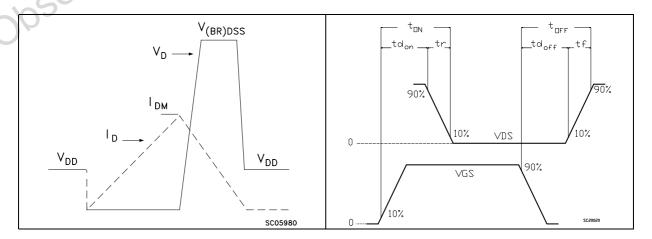


Figure 22. Unclamped inductive waveform

Figure 23. Switching time waveform



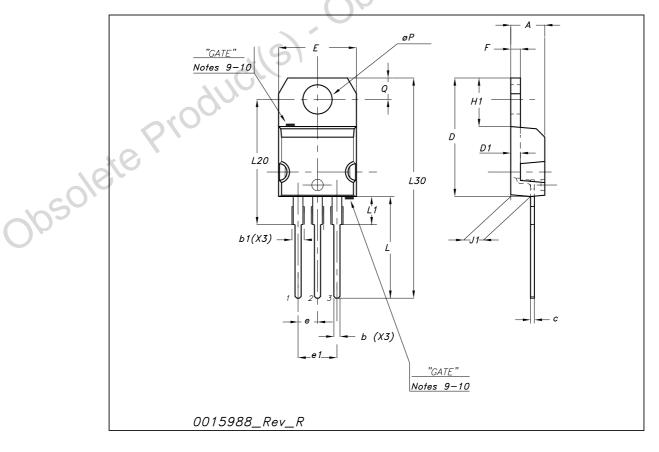
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>

Obsolete Product(s).

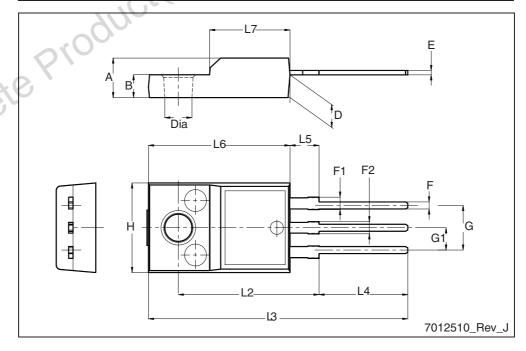
#### TO-220 mechanical data

Dim		mm		inch			
Dim	Min	Тур	Max	Min	Тур	Max	
A	4.40		4.60	0.173		0.181	
b	0.61		0.88	0.024		0.034	
b1	1.14		1.70	0.044		0.066	
С	0.48		0.70	0.019		0.027	
D	15.25		15.75	0.6		0.62	
D1		1.27			0.050		
E	10		10.40	0.393		0.409	
е	2.40		2.70	0.094	X	0.106	
e1	4.95		5.15	0.194	(0)	0.202	
F	1.23		1.32	0.048	AU	0.051	
H1	6.20		6.60	0.244	10	0.256	
J1	2.40		2.72	0.094	)	0.107	
L	13		14	0.511		0.551	
L1	3.50		3.93	0.137		0.154	
L20		16.40	101		0.645		
L30		28.90	7/0		1.137		
ØP	3.75		3.85	0.147		0.151	
Q	2.65		2.95	0.104		0.116	



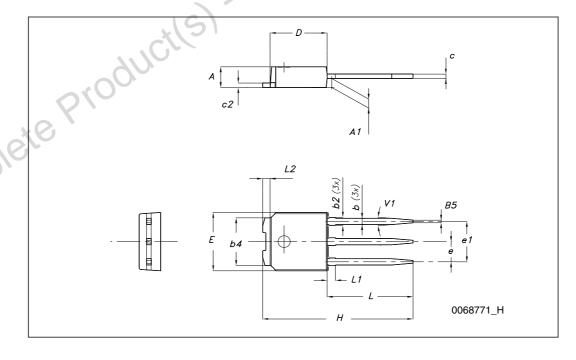
#### TO-220FP mechanical data

Dim.		mm					
Dim.	Min.	Тур.	Max.				
А	4.4		4.6				
В	2.5		2.7				
D	2.5		2.75				
Е	0.45		0.7				
F	0.75		1				
F1	1.15		1.70				
F2	1.15		1.5				
G	4.95		5.2				
G1	2.4		2.7				
Н	10	No.	10.4				
L2		16					
L3	28.6		30.6				
L4	9.8	120	10.6				
L5	2.9	10	3.6				
L6	15.9		16.4				
L7	9		9.3				
Dia	3		3.2				



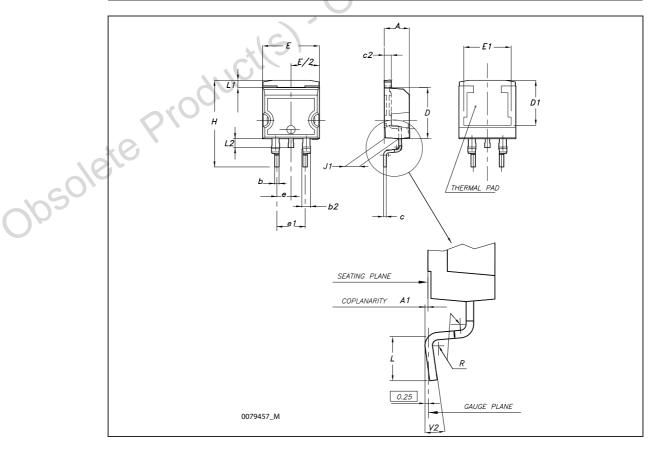
### TO-251 (IPAK) mechanical data

DIM.		mm.				
DIIVI.	min.	typ	max.			
Α	2.20		2.40			
A1	0.90		1.10			
b	0.64		0.90			
b2			0.95			
b4	5.20		5.40			
С	0.45		0.60			
c2	0.48		0.60			
D	6.00		6.20			
E	6.40		6.60			
е		2.28				
e1	4.40		4.60			
Н		16.10				
L	9.00	7/0,	9.40			
(L1)	0.80	60'	1.20			
L2		0.80				
V1		10 °				



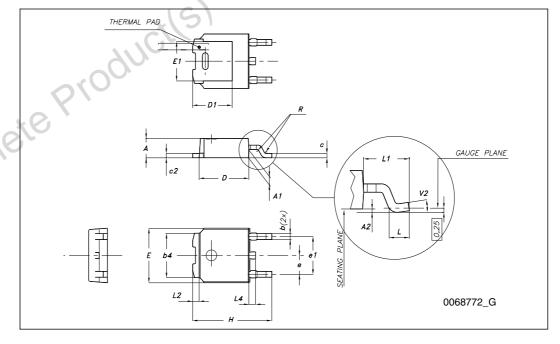
### D<sup>2</sup>PAK (TO-263) mechanical data

Dim		mm			inch			
Dilli	Min	Тур	Max	Min	Тур	Max		
Α	4.40		4.60	0.173		0.181		
A1	0.03		0.23	0.001		0.009		
b	0.70		0.93	0.027		0.037		
b2	1.14		1.70	0.045		0.067		
С	0.45		0.60	0.017		0.024		
c2	1.23		1.36	0.048		0.053		
D	8.95		9.35	0.352		0.368		
D1	7.50			0.295	3	101		
E	10		10.40	0.394		0.409		
E1	8.50			0.334	7116	,		
е		2.54			0.1			
e1	4.88		5.28	0.192	0	0.208		
Н	15		15.85	0.590		0.624		
J1	2.49		2.69	0.099		0.106		
L	2.29		2.79	0.090		0.110		
L1	1.27		1.40	0.05		0.055		
L2	1.30		1.75	0.051		0.069		
R		0.4	72		0.016			
V2	0°		8°	0°		8°		



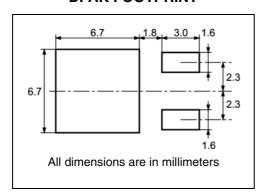
### TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
Α	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	.00
е		2.28	
e1	4.40		4.60
Н	9.35	201	10.10
L	1	10.	
L1		2.80	
L2		0.80	
L4	0.60	703	1
R		0.20	
V2	0 0		8 °

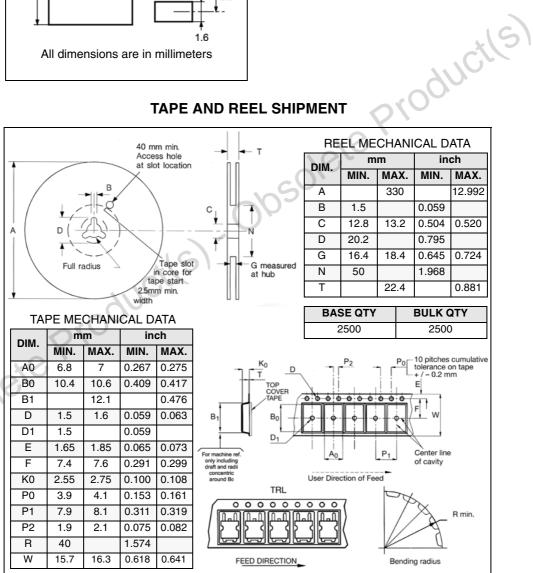


#### Packaging mechanical data 5

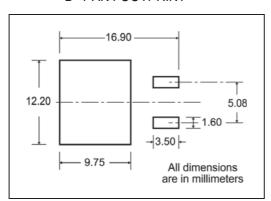
#### **DPAK FOOTPRINT**



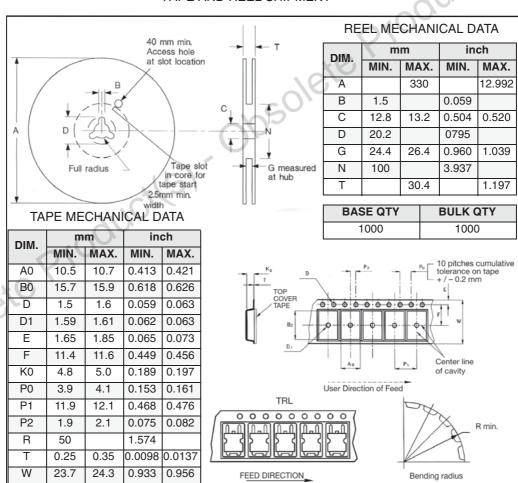
#### TAPE AND REEL SHIPMENT



## D<sup>2</sup>PAK FOOTPRINT



### TAPE AND REEL SHIPMENT



Revision history STx8NM60N

# 6 Revision history

Table 9. Document revision history

Date	Revision	Changes
29-Aug-2007	1	First release
07-Jan-2008	2	I <sub>DSS</sub> value has been corrected on <i>Table 5: On/off states</i>
21-Nov-2008	3	Added new package, mechanical data.

Obsolete Product(s). Obsolete Product(s)

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